

P-Channel Enhancement Mode Power MOSFET

Description

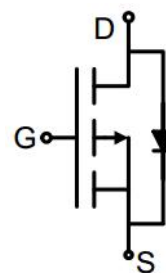
The GT100P10TL uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

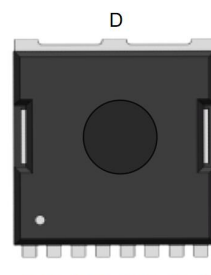
- V_{DS} -100V
- I_D (at $V_{GS} = -10V$) -185A
- $R_{DS(ON)}$ (at $V_{GS} = -10V$) < 9m Ω
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters



Schematic diagram

G₁ S₂ S₃ S₄ S₅ S₆ S₇ S₈

TOLL-8L

Ordering Information

Device	Package	Marking	Packaging
GT100P10TL	TOLL-8L	GT100P10	2000pcs/Reel

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-100	V
Continuous Drain Current	I_D	$T_C = 25^\circ\text{C}$ -185	A
		$T_C = 100^\circ\text{C}$ -117	
Pulsed Drain Current (note1)	I_{DM}	-740	A
Gate-Source Voltage	V_{GS}	± 20	V
Power Dissipation	P_D	385	W
Single pulse avalanche energy (note2)	E_{AS}	1056	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	50	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case	R_{thJC}	0.32	$^\circ\text{C/W}$

Specifications T _J = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-100	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -100V, V _{GS} = 0V	--	--	-1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±20V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-2.0	-3.5	-5.0	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = -10V, I _D = -40A	--	7.5	9.0	mΩ
Forward Transconductance	g _{FS}	V _{DS} = -5V, I _D = -40A	--	44	--	S
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = -50V, f = 1.0MHz	--	12200	--	pF
Output Capacitance	C _{oss}		--	1050	--	
Reverse Transfer Capacitance	C _{rss}		--	65	--	
Total Gate Charge	Q _g	V _{DD} = -50V, I _D = -40A, V _{GS} = -10V	--	184	--	nC
Gate-Source Charge	Q _{gs}		--	32	--	
Gate-Drain Charge	Q _{gd}		--	24	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = -50V, I _D = -40A, R _G = 1.6Ω	--	44	--	ns
Turn-on Rise Time	t _r		--	36	--	
Turn-off Delay Time	t _{d(off)}		--	160	--	
Turn-off Fall Time	t _f		--	44	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25°C	--	--	-185	A
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = -40A, V _{GS} = 0V	--	--	-1.2	V
Reverse Recovery Charge	Q _{rr}	I _F = -40A, V _{GS} = 0V di/dt=-100A/us	--	320	--	nC
Reverse Recovery Time	T _{rr}		--	176	--	ns

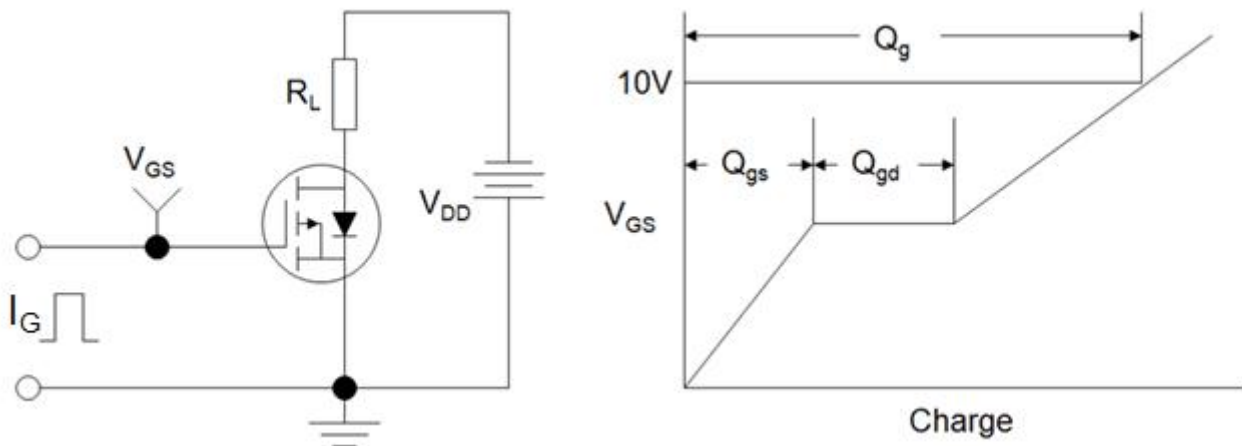
Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. EAS condition : $T_J = 25^{\circ}\text{C}$, $V_{DD} = -50V$, $V_{GS} = -10V$, $L = 0.5mH$, $R_g = 25\Omega$

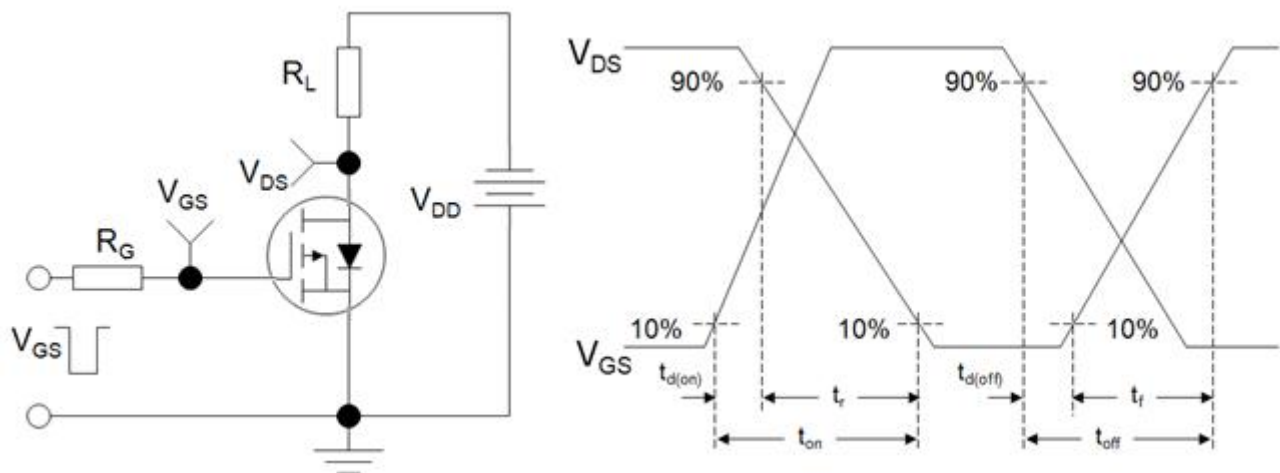
The table shows the minimum avalanche energy, which is 2910mJ when the device is tested until failure

3. Identical low side and high side switch with identical R_G

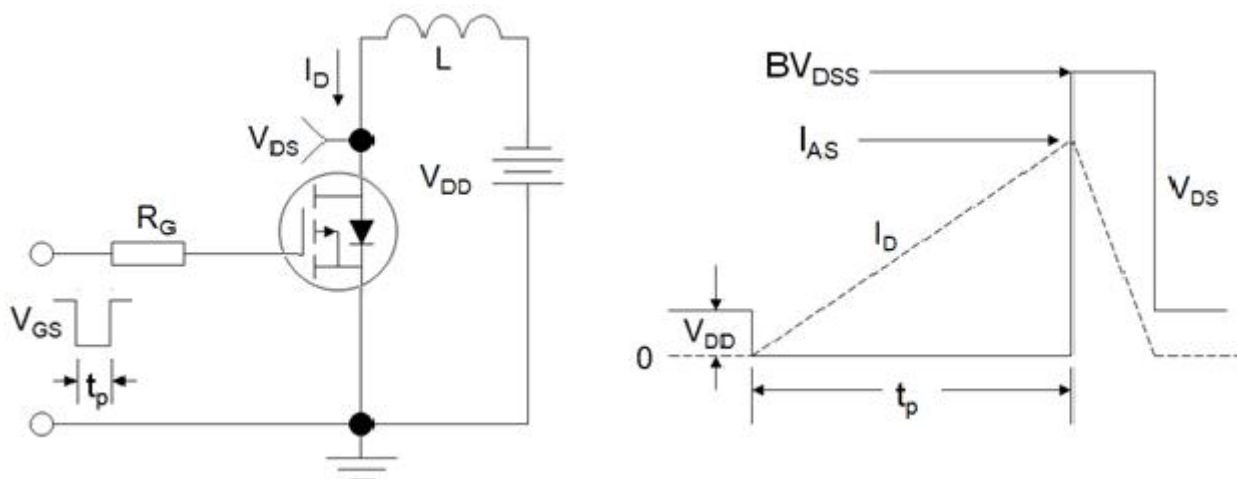
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

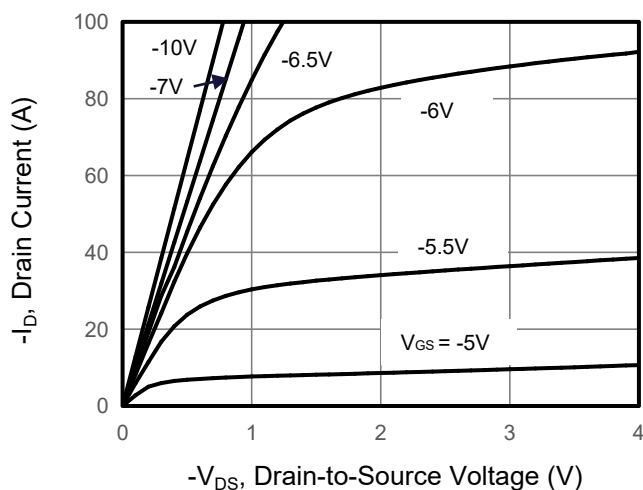


Figure 2. Transfer Characteristics

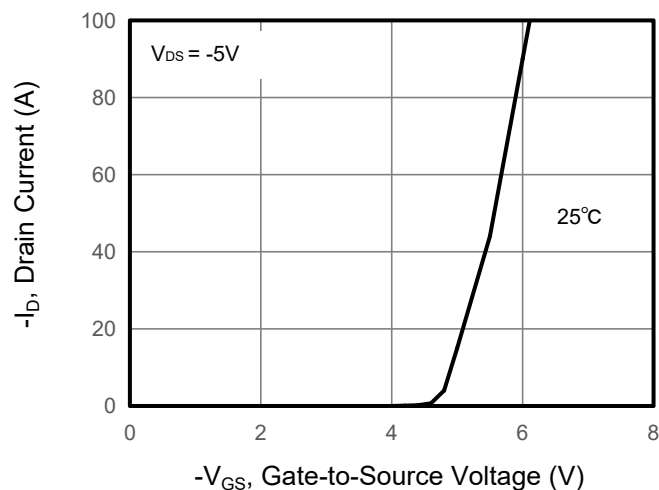


Figure 3. Drain Source On Resistance

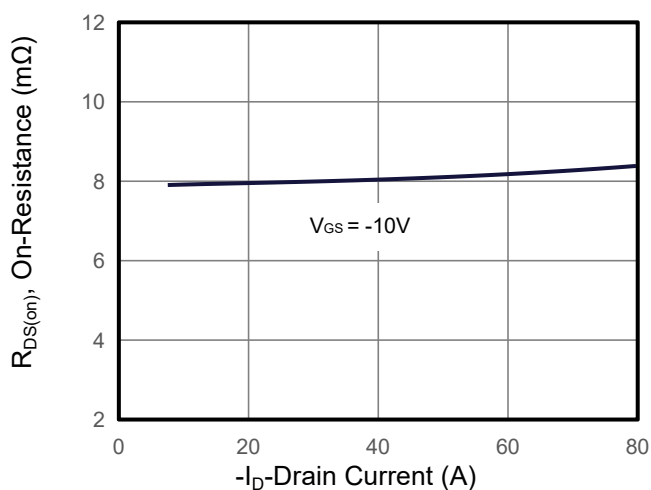


Figure 4. Gate Charge

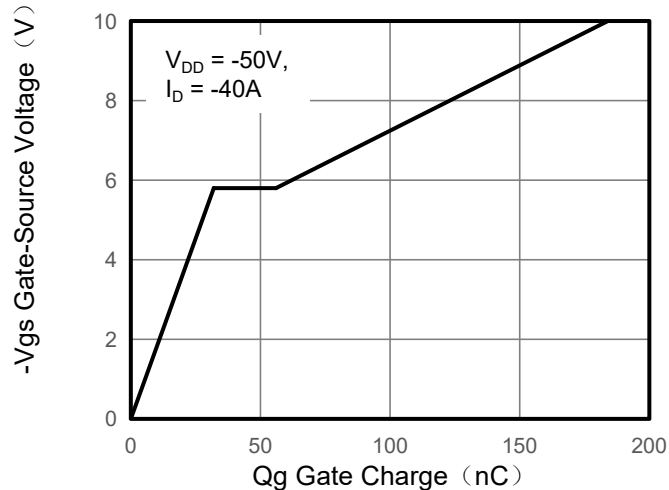


Figure 5. Capacitance

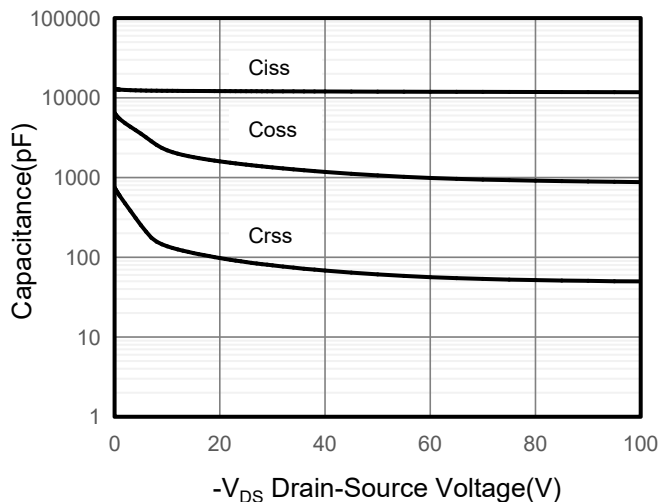
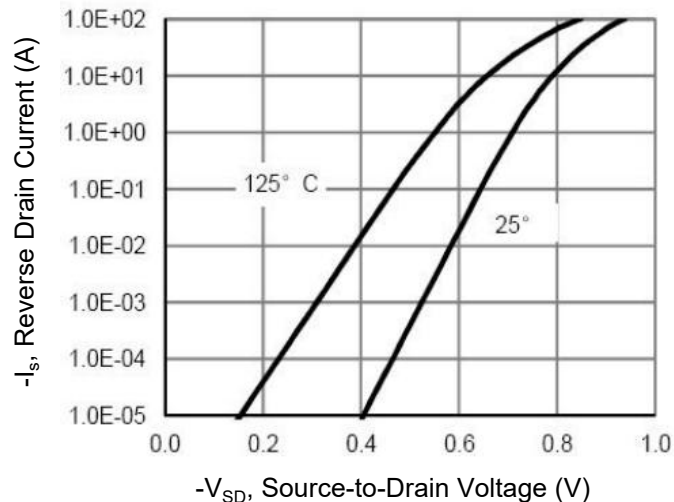


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

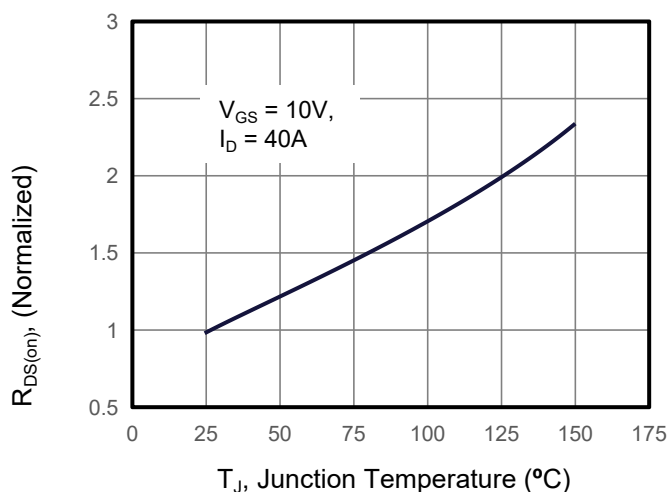


Figure 8. Safe Operation Area

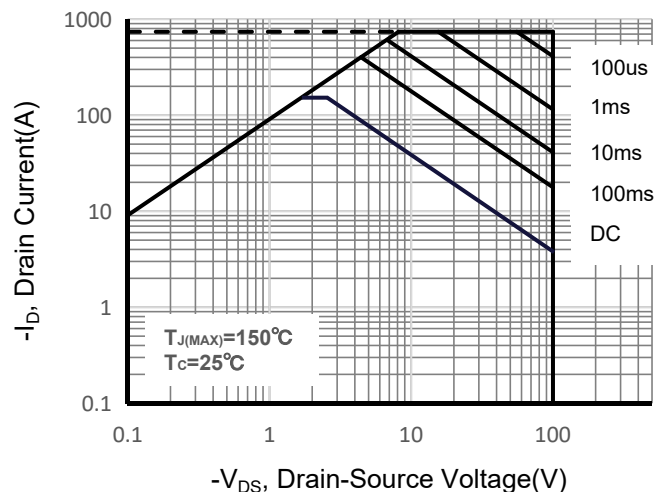


Figure 9. Maximum Continuous Drain Current vs Case Temperature

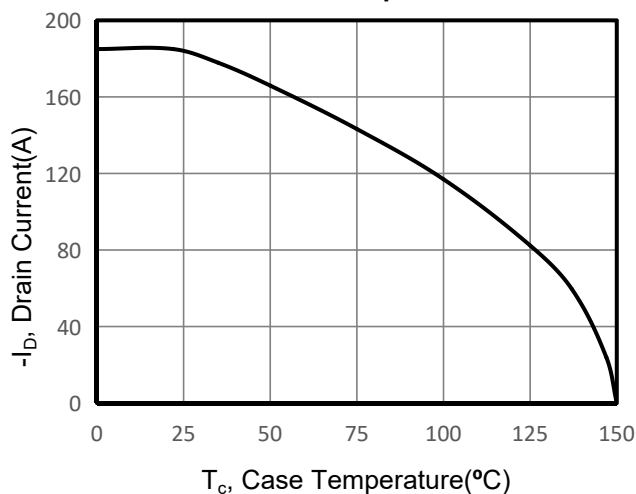
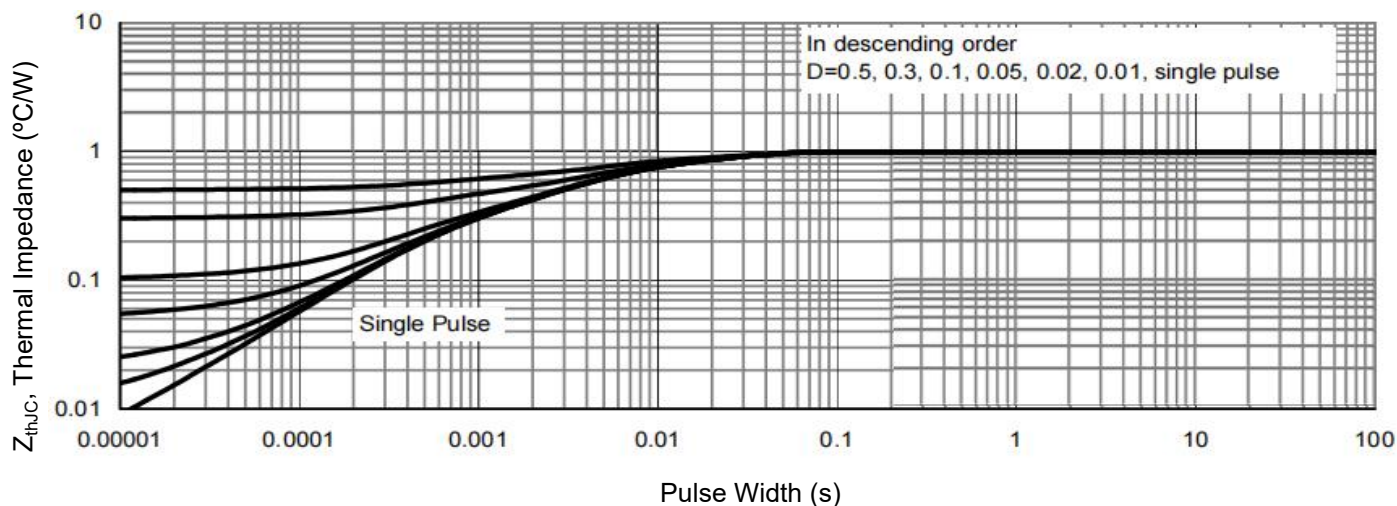
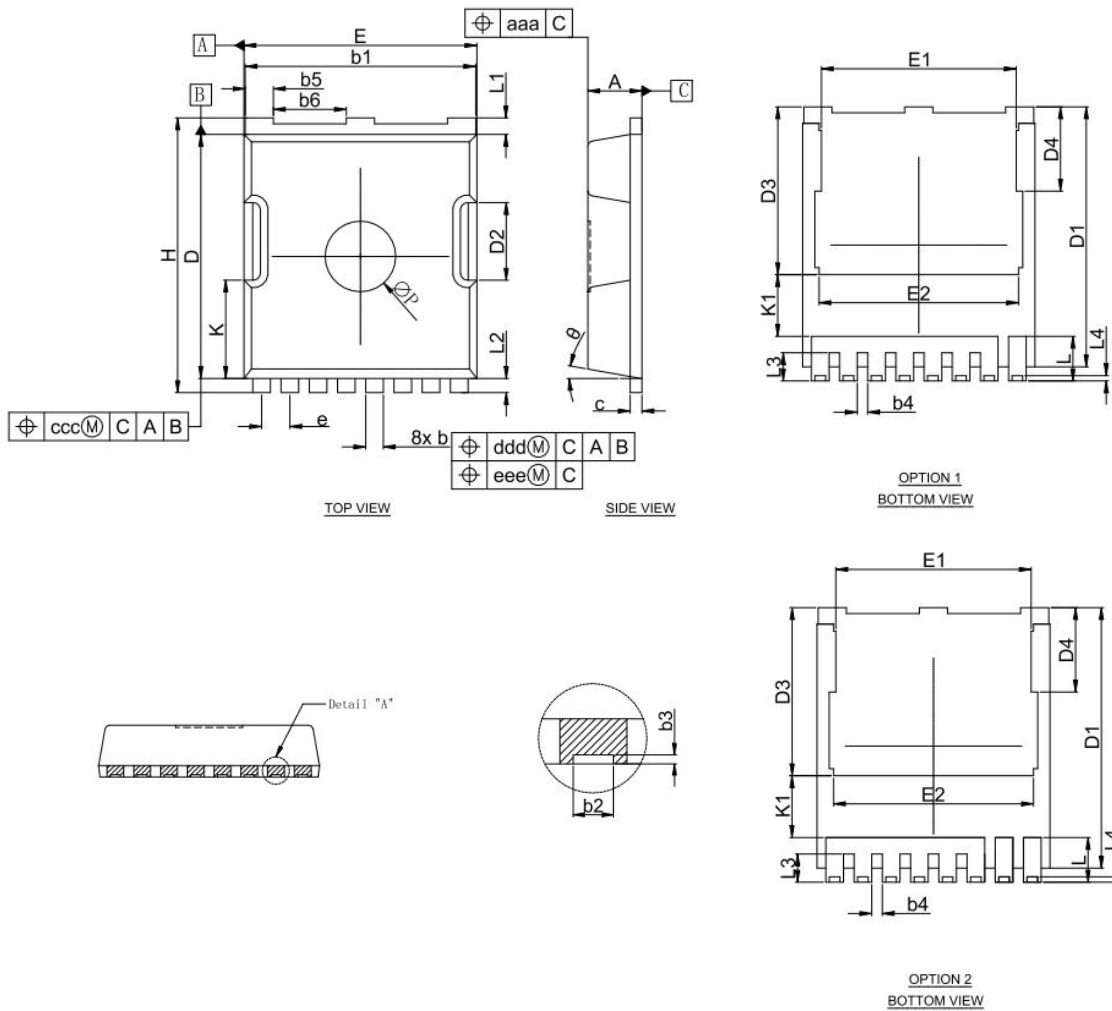


Figure 10. Normalized Maximum Transient Thermal Impedance



TOLL-8L Package Information



SYMBOL	COMMON			SYMBOL	COMMON		
	MILLIMETER				MILLIMETER		
	MIN.	NOMINAL	MAX.		MIN.	NOMINAL	MAX.
A	2.20	2.30	2.40	E1	8.20	8.30	8.40
b	0.70	0.80	0.90	E2	8.35	8.50	8.65
b1	9.70	9.80	9.90	H	11.50	11.68	11.85
b2	0.36	0.45	0.55	K	4.08	4.18	4.28
b3	0.05	0.10	0.35	K1	2.45	---	---
b4	0.30	0.40	0.50	L	1.60	1.90	2.10
b5	1.10	1.20	1.30	L1	0.50	0.70	0.90
b6	3.00	3.10	3.20	L2	0.50	0.60	0.70
c	0.40	0.50	0.60	L3	1.00	1.20	1.30
D	10.28	10.38	10.55	L4	0.13	0.23	0.33
D1	10.98	11.08	11.18	P	2.85	3.00	3.15
D2	3.20	3.30	3.40	θ	10° REF		
D3	7.00	7.15	7.30	aaa	0.20		
D4	3.44	3.59	3.74	ccc	0.20		
e	1.10	1.20	1.30	ddd	0.25		
E	9.80	9.90	10.00	eee	0.20		